

2SB1574 (Tentative)

Silicon PNP epitaxial planar type

For low-frequency output amplification

Features

- Possible to solder radiation fin directly to printed circuit board
- Type with universal characteristics
- Collector breakdown voltage: $V_{CBO}/V_{CEO} = -50V$
- Collector current: $I_C = -2A$

Absolute Maximum Ratings ($T_C=25^\circ C$)

Parameter	Symbol	Rated	Unit
Collector to base voltage	V_{CBO}	-50	V
Collector to emitter voltage	V_{CEO}	-50	V
Emitter to base voltage	V_{EBO}	-5	V
Peak collector current	I_{CP}	-3	A
Collector current	I_C	-2	A
Collector power dissipation ($T_C=25^\circ C$)	P_C	10	W
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

Electrical Characteristics ($T_C=25^\circ C$)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -10V, I_E = 0$			-0.1	μA
Collector to base voltage	V_{CBO}	$I_C = -10\mu A, I_E = 0$	-50			V
Collector to emitter voltage	V_{CEO}	$I_C = -1mA, I_B = 0$	-50			V
Emitter to base voltage	V_{EBO}	$I_E = -10\mu A, I_C = 0$	-5			V
Forward current transfer ratio	h_{FE1}^*	$V_{CE} = -2V, I_C = -200mA$	120		340	
	h_{FE2}	$V_{CE} = -2V, I_C = -1A$	60			
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1A, I_B = -50mA$		-0.2	-0.3	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = -1A, I_B = -50mA$		-0.85	-1.2	V
Transition frequency	f_T	$V_{CB} = -10V, I_E = 50mA, f = 200MHz$		80		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		45	60	pF

* h_{FE1} Rank classification

Rank	R	S
h_{FE1}	120 to 240	170 to 340

